

Ann Witvrouw

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

155
papers

1,844
citations

20
h-index

37
g-index

178
ext. papers

2,103
ext. citations

2.8
avg, IF

4.51
L-index

#	Paper	IF	Citations
155	3D total variation denoising in X-CT imaging applied to pore extraction in additively manufactured parts. <i>Measurement Science and Technology</i> , 2022 , 33, 045602	2	1
154	Melt pool feature analysis using a high-speed coaxial monitoring system for laser powder bed fusion of Ti-6Al-4V grade 23. <i>International Journal of Advanced Manufacturing Technology</i> , 2022 , 120, 6497	3.2	0
153	A novel tomographic characterisation approach for sag and dross defects in metal additively manufactured channels. <i>Additive Manufacturing</i> , 2021 , 39, 101892	6.1	0
152	A Micro-Computed Tomography Comparison of the Porosity in Additively Fabricated CuCr1 Alloy Parts Using Virgin and Surface-Modified Powders. <i>Materials</i> , 2021 , 14,	3.5	1
151	Improving the quality of up-facing inclined surfaces in laser powder bed fusion of metals using a dual laser setup. <i>Procedia CIRP</i> , 2020 , 94, 266-269	1.8	5
150	Keyhole-induced porosities in Laser-based Powder Bed Fusion (L-PBF) of Ti6Al4V: High-fidelity modelling and experimental validation. <i>Additive Manufacturing</i> , 2019 , 30, 100835	6.1	78
149	On the influence of laser defocusing in Selective Laser Melting of 316L. <i>Additive Manufacturing</i> , 2018 , 23, 161-169	6.1	86
148	Thermal simulation of the cooling down of selective laser sintered parts in PA12. <i>Rapid Prototyping Journal</i> , 2018 , 24, 1117-1123	3.8	5
147	Thickness effect on the structural and electrical properties of poly-SiGe films. <i>Materials Research Bulletin</i> , 2014 , 49, 102-107	5.1	4
146	Quantifying the Aggregation Factor in Carbon Nanotube Dispersions by Absorption Spectroscopy. <i>Journal of Nanoscience</i> , 2014 , 2014, 1-13		6
145	Poly-SiGe for MEMS-above-CMOS Sensors. <i>Springer Series in Advanced Microelectronics</i> , 2014 ,	1	1
144	Influence of germanium incorporation on the structural and electrical properties of boron-doped ultrathin poly-Si _{1-x} Ge _x films deposited by chemical vapour deposition. <i>Applied Physics A: Materials Science and Processing</i> , 2014 , 116, 751-757	2.6	5
143	Design of a Poly-SiGe Piezoresistive Pressure Sensor. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 51-73	1	
142	Poly-SiGe as Piezoresistive Material. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 25-49	1	
141	The Pressure Sensor Fabrication Process. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 75-99	1	
140	Sealing of Surface Micromachined Poly-SiGe Cavities. <i>Springer Series in Advanced Microelectronics</i> , 2014 , 101-126	1	
139	Improving the selectivity by using different blocking agents in DNA hybridization assays for SiGe bio-molecular sensors. <i>Microelectronic Engineering</i> , 2013 , 111, 421-424	2.5	14

138	A 2D MEMS grating based CMOS compatible poly-SiGe variable optical attenuator. <i>Microelectronic Engineering</i> , 2013 , 105, 8-12	2.5	1
137	Towards CMOS-compatible single-walled carbon nanotube resonators. <i>Microelectronic Engineering</i> , 2013 , 107, 219-222	2.5	6
136	Multi-response optimization of ultrathin poly-SiGe films characteristics for Nano-ElectroMechanical Systems (NEMS) using the grey-Taguchi technique. <i>Microelectronic Engineering</i> , 2013 , 111, 229-233	2.5	9
135	Meta-materials approach to sensitivity enhancement of MEMS BAW resonant sensors 2013 ,		3
134	Design of SiGe Nano-Electromechanical relays for logic applications 2013 ,		1
133	Dedicated test structure for the measurement of adhesion forces between contacting surfaces in MEMS devices 2013 ,		5
132	Static and dynamic characterization of pull-in protected CMOS compatible poly-SiGe grating light valves. <i>Sensors and Actuators A: Physical</i> , 2012 , 179, 283-290	3.9	3
131	Poly-SiGe-Based MEMS Thin-Film Encapsulation. <i>Journal of Microelectromechanical Systems</i> , 2012 , 21, 110-120	2.5	15
130	Dielectrophoretic assembly of suspended single-walled carbon nanotubes. <i>Microelectronic Engineering</i> , 2012 , 98, 218-221	2.5	8
129	SiGe MEMS Accelerometers Combining a Large Bandwidth with a High Capacitive Sensitivity. <i>Procedia Engineering</i> , 2012 , 47, 742-745		4
128	Comparison of three methods to measure the internal pressure of empty MEMS packages 2012 ,		3
127	2012 ,		1
126	CMOS compatible polycrystalline silicongermanium based pressure sensors. <i>Sensors and Actuators A: Physical</i> , 2012 , 188, 9-18	3.9	16
125	Investigation of temporary stiction in poly-SiGe micromirror arrays. <i>Sensors and Actuators A: Physical</i> , 2012 , 188, 320-328	3.9	2
124	SiGe MEMS at processing temperatures below 250°C. <i>Sensors and Actuators A: Physical</i> , 2012 , 188, 230-239		5
123	Study of glass frit induced stiction using a micromirror array. <i>Microelectronics Reliability</i> , 2012 , 52, 2256-2260		1
122	Effect of the functionalization process on the performance of SiGe MEM resonators used for bio-molecular sensing. <i>Microelectronics Reliability</i> , 2012 , 52, 2272-2277	1.2	4
121	MEMS packaging and reliability: An undividable couple. <i>Microelectronics Reliability</i> , 2012 , 52, 2228-2234	1.2	14

120	CMOS-Integrated Poly-SiGe Piezoresistive Pressure Sensor. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1204-1206	1.4	18
119	A Detailed Study of a Novel Wafer Separation Method for Surface Sensitive MEMS Wafers. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1415, 1		0
118	Temporary 0-Level MEMS Packaging Using a Heat Decomposable Sealing Ring. <i>Procedia Engineering</i> , 2011 , 25, 1497-1500		
117	A Parylene Temporary Packaging Technique for MEMS Wafer Handling. <i>Procedia Engineering</i> , 2011 , 25, 1501-1504		1
116	Above-IC generic poly-SiGe thin film wafer level packaging and MEM device technology: Application to accelerometers 2011 ,		10
115	Outgassing study of thin films used for poly-SiGe based vacuum packaging of MEMS. <i>Microelectronics Reliability</i> , 2011 , 51, 1878-1881	1.2	8
114	Enabling poly-SiGe MEMS scaling by improving anchor strength and resistance. <i>Microelectronic Engineering</i> , 2011 , 88, 2420-2423	2.5	
113	A CMOS compatible polycrystalline silicon-germanium based piezoresistive pressure sensor 2011 ,		7
112	A wafer-level poly-sige-based thin film packaging technology demonstrated on a soi-based high-Q MEM resonator 2011 ,		1
111	Contact Resistivity of Laser Annealed SiGe for MEMS Structural Layers Deposited at 210°C. <i>Materials Research Society Symposia Proceedings</i> , 2011 , 1299, 1		
110	An in-plane SiGe differential capacitive accelerometer for above-IC integration. <i>Journal of Micromechanics and Microengineering</i> , 2011 , 21, 074011	2	8
109	Sealing of poly-SiGe surface micromachined cavities for MEMS-above-CMOS applications. <i>Journal of Micromechanics and Microengineering</i> , 2011 , 21, 115019	2	3
108	Stiction-free poly-SiGe resonators for monolithic integration of biosensors with CMOS 2011 ,		6
107	Thin film encapsulated SiGe accelerometer for MEMS above IC integration 2011 ,		3
106	Investigation of temporary stiction in poly-SiGe micromirror arrays 2011 ,		3
105	Physical loss mechanisms for resonant acoustical waves in boron doped poly-SiGe deposited with hydrogen dilution. <i>Journal of Applied Physics</i> , 2010 , 108, 084517	2.5	4
104	Piezoresistivity and electrical properties of poly-SiGe deposited at CMOS-compatible temperatures 2010 ,		1
103	Improvement of PECVD SiliconGermanium Crystallization for CMOS Compatible MEMS Applications. <i>Journal of the Electrochemical Society</i> , 2010 , 157, D103	3.9	11

102	(Invited) SiGe MEMS Technology: A Platform Technology Enabling Different Demonstrators. <i>ECS Transactions</i> , 2010 , 33, 799-812	1	9
101	Wafer Level Characterization of the Sacrificial HDP Oxide Lateral Etching by Anhydrous Vapor HF with Ethanol Vapor for SiGe MEMS Structures. <i>ECS Transactions</i> , 2010 , 33, 295-307	1	4
100	Apparent and steady-state etch rates in thin film etching and under-etching of microstructures: II. Characterization. <i>Journal of Micromechanics and Microengineering</i> , 2010 , 20, 055034	2	3
99	Apparent and steady-state etch rates in thin film etching and under-etching of microstructures: I. Modelling. <i>Journal of Micromechanics and Microengineering</i> , 2010 , 20, 055033	2	3
98	Improvement of the poly-SiGe electrode contact technology for MEMS. <i>Journal of Micromechanics and Microengineering</i> , 2010 , 20, 095029	2	6
97	Mechanical characterization of poly-SiGe layers for CMOS/MEMS integrated application. <i>Journal of Micromechanics and Microengineering</i> , 2010 , 20, 015014	2	12
96	Evaluation of the piezoresistive and electrical properties of polycrystalline silicon-germanium for MEMS sensor applications 2010 ,		3
95	Influence of the novel anchor design on the shear strength of poly-sige thin film wafer level packages 2010 ,		1
94	Light sensitive SiGe MEM resonator for detection and frequency tuning applications. 2010 ,		7
93	. <i>Journal of Microelectromechanical Systems</i> , 2010 , 19, 202-214	2.5	19
92	Development, Optimization and Evaluation of a CF4 Pretreatment Process to Remove Unwanted Interfacial Layers in Stacks of CVD and PECVD Polycrystalline Silicon-Germanium for MEMS Applications. <i>ECS Transactions</i> , 2010 , 28, 79-90	1	9
91	Design and characterization of a CMOS compatible poly-SiGe lowg capacitive accelerometer. <i>Procedia Engineering</i> , 2010 , 5, 742-745		4
90	SiGe based grating light valves: A leap towards monolithic integration of MOEMS. <i>Microelectronic Engineering</i> , 2010 , 87, 1195-1197	2.5	3
89	Novel micromirror design with variable pull-in voltage. <i>Microelectronic Engineering</i> , 2010 , 87, 1248-1252	2.5	1
88	Ultra-high density MEMS probe memory device. <i>Microelectronic Engineering</i> , 2010 , 87, 1198-1203	2.5	13
87	Packaging of 11 MPixel CMOS-Integrated SiGe Micro-Mirror Arrays 2009 ,		5
86	CMOS-integrated poly-SiGe cantilevers with read/write system for probe storage device 2009 ,		12
85	CMOS-integrated sige MEMS: Application to micro-mirrors 2009 ,		1

84	Simultaneous Optimization of the Material Properties, Uniformity and Deposition Rate of Polycrystalline CVD and PECVD Silicon-Germanium Layers for MEMS Applications. <i>ECS Transactions</i> , 2009 , 16, 353-364	1	11
83	Evaluation of the Electrical Properties, Piezoresistivity and Noise of poly-SiGe for MEMS-above-CMOS applications. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1153, 1		1
82	Polycrystalline Silicon-Germanium Electrode Contact Technology Improvement for MEMS Applications. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1222, 1		1
81	Laser-induced Crystallization of SiGe MEMS Structural Layers Deposited at Temperatures below 250°C. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1153, 1		1
80	SLM device for 193nm lithographic applications. <i>Microelectronic Engineering</i> , 2009 , 86, 569-572	2.5	8
79	CMOSMEMS integration today and tomorrow. <i>Scripta Materialia</i> , 2008 , 59, 945-949	5.6	30
78	Determination of the piezoresistivity of microcrystalline silicon-germanium and application to a pressure sensor 2008 ,		4
77	A novel gap narrowing process for creating high aspect ratio transduction gaps for MEM HF Resonators. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1139, 1		1
76	The influence of geometrical imperfections in micromachined cantilevers on the extracted Young's modulus using a simple model. <i>Journal of Micromechanics and Microengineering</i> , 2008 , 18, 115027	2	4
75	The Road To Flexible Mems Integration. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1075, 1		4
74	Stacked Boron Doped Poly-Crystalline Silicon-Germanium Layers: an Excellent MEMS Structural Material. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1075, 1		2
73	Wafer level characterization and failure analysis of microsensors and actuators 2008 ,		4
72	Highly reliable CMOS-integrated 11MPixel SiGe-based micro-mirror arrays for high-end industrial applications 2008 ,		13
71	Long-term reliability measurements on MEMS using a laser-Doppler vibrometer 2008 ,		5
70	High throughput measurement techniques for wafer level yield inspection of MEMS devices 2008 ,		5
69	A new generic surface micromachining module for MEMS hermetic packaging at temperatures below 200 °C. <i>Microsystem Technologies</i> , 2007 , 13, 1451-1456	1.7	5
68	. <i>Journal of Microelectromechanical Systems</i> , 2007 , 16, 581-588	2.5	9
67	Highly reliable and extremely stable SiGe micro-mirrors 2007 ,		5

66	Fabrication of Porous Membranes for MEMS Packaging by One-Step Anodization in Sulfuric Acid. <i>Journal of the Electrochemical Society</i> , 2007 , 154, K74	3.9	18
65	Kinetic to Transport-Limited Anhydrous HF Etching of Silicon Oxynitride Films in Supercritical CO ₂ . <i>Journal of Physical Chemistry C</i> , 2007 , 111, 15251-15257	3.8	8
64	A 10 μm thick poly-SiGe gyroscope processed above 0.35 μm CMOS 2007 ,		8
63	CMOS-MEMS integration. <i>IEEE/ACM International Conference on Computer-Aided Design, Digest of Technical Papers</i> , 2006 ,		7
62	Low Thermal Budget Techniques For Controlling Stress In Si _{1-x} Ge _x Deposited At 210°C. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 910, 14		
61	CMOS-MEMS Integration: Why, How and What?. <i>IEEE/ACM International Conference on Computer-Aided Design, Digest of Technical Papers</i> , 2006 ,		11
60	Characterization and strain gradient optimization of PECVD poly-SiGe layers for MEMS applications. <i>Sensors and Actuators A: Physical</i> , 2006 , 130-131, 403-410	3.9	23
59	Characterization of KrF excimer laser annealed PECVD Si _{0.8} Ge _{0.2} for MEMS post-processing. <i>Sensors and Actuators A: Physical</i> , 2006 , 127, 316-323	3.9	20
58	Creep-resistant aluminum alloys for use in MEMS. <i>Journal of Micromechanics and Microengineering</i> , 2005 , 15, S165-S170	2	31
57	SIGEM, low-temperature deposition of poly-SiGe MEMS structures on standard CMOS circuits (Invited Paper) 2005 ,		2
56	Determination of stress profile and optimization of stress gradient in PECVD poly-SiGe films. <i>Sensors and Actuators A: Physical</i> , 2005 , 118, 313-321	3.9	9
55	The Use of Functionally Graded Poly-SiGe Layers for MEMS Applications. <i>Materials Science Forum</i> , 2005 , 492-493, 255-260	0.4	202
54	Metal induced crystallization of SiGe at 370°C for monolithically integrated MEMS applications. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 808, 12		4
53	Physics. The best materials for tiny, clever sensors. <i>Science</i> , 2004 , 306, 986-7	33.3	15
52	Self-aligned 0-level sealing of MEMS devices by a two layer thin film reflow process. <i>Microsystem Technologies</i> , 2004 , 10, 364-371	1.7	1
51	Materials issues in the processing, the operation and the reliability of MEMS. <i>Microelectronic Engineering</i> , 2004 , 76, 245-257	2.5	47
50	Creep as a reliability problem in MEMS. <i>Microelectronics Reliability</i> , 2004 , 44, 1733-1738	1.2	36
49	The novel use of low temperature hydrogenated microcrystalline silicon germanium (μSiGe:H) for MEMS applications. <i>Microelectronic Engineering</i> , 2004 , 76, 266-271	2.5	12

48	Stable thin film encapsulation of acceleration sensors using polycrystalline silicon as sacrificial and encapsulation layer. <i>Sensors and Actuators A: Physical</i> , 2004 , 114, 355-361	3.9	20
47	Creep characterization of Al alloy thin films for use in MEMS applications. <i>Microelectronic Engineering</i> , 2004 , 76, 272-278	2.5	38
46	Effect of deposition parameters on the stress gradient of CVD and PECVD poly-SiGe for MEMS applications 2004 ,		7
45	Poly-SiGe, a superb material for MEMS. <i>Materials Research Society Symposia Proceedings</i> , 2003 , 782, 1		7
44	New low-stress PECVD poly-SiGe Layers for MEMS. <i>Journal of Microelectromechanical Systems</i> , 2003 , 12, 816-825	2.5	27
43	Poly SiGe, a promising material for MEMS monolithic integration with the driving electronics. <i>Sensors and Actuators A: Physical</i> , 2002 , 97-98, 503-511	3.9	35
42	Characterization of Reduced-pressure Chemical Vapor Deposition Polycrystalline Silicon Germanium Deposited at Temperatures 550 °C. <i>Journal of Materials Research</i> , 2002 , 17, 1580-1586	2.5	7
41	Sputtered Tantalum as a Structural Material for Surface Micromachined RF Switches. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 729, 331		3
40	Experimental determination of the maximum post-process annealing temperature for standard CMOS wafers. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 377-385	2.9	99
39	Planarization of deep trenches 2001 , 4557, 49		2
38	Effect of in situ boron doping on properties of silicon germanium films deposited by chemical vapor deposition at 400 °C. <i>Journal of Materials Research</i> , 2001 , 16, 2607-2612	2.5	22
37	Poly SiGe, a Promising Material for MEMS Post-Processing on Top of Standard CMOS Wafers 2001 , 960-963		
36	Effect of Deposition Conditions on the Structural and Mechanical Properties of Poly SiGe. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 609, 851		4
35	Effect of oxide and W-CMP on the material properties and electromigration behaviour of layered aluminum metallisations. <i>Microelectronic Engineering</i> , 2000 , 50, 291-299	2.5	6
34	Integration of HSQ in the direct-on-metal approach for 0.25-µm technology. <i>Microelectronic Engineering</i> , 2000 , 50, 349-355	2.5	2
33	Why CMOS-integrated transducers? A review. <i>Microsystem Technologies</i> , 2000 , 6, 192-199	1.7	22
32	Comparison between wet HF etching and vapor HF etching for sacrificial oxide removal 2000 , 4174, 130		55
31	Electromigration-induced drift in damascene and plasma-etched Al(Cu). I. Kinetics of Cu depletion in polycrystalline interconnects. <i>Journal of Applied Physics</i> , 2000 , 87, 86-98	2.5	11

30	The kinetics of the early stages of electromigration and concurrent temperature induced processes in thin film metallisations studied by means of an in-situ high resolution resistometric technique. <i>Microelectronics Reliability</i> , 1999 , 39, 1657-1665	1.2	1
29	Modeling and microstructural characterization of incubation, time-dependent drift and saturation during electromigration in AlSiCu stripes. <i>Microelectronics Reliability</i> , 1999 , 39, 1603-1616	1.2	3
28	Fabrication and reliability testing of Ti/TiN heaters 1999 ,		8
27	Effect of Cu on Al Interfacial Mass Transport in Bamboo Rie and Damascene Al(Cu). <i>Materials Research Society Symposia Proceedings</i> , 1999 , 563, 91		1
26	Stress Relaxation in AlCu and AlSiCu Thin Films. <i>Journal of Materials Research</i> , 1999 , 14, 1246-1254	2.5	14
25	Overview of the kinetics of the early stages of electromigration under low (= realistic) current density stress. <i>Microelectronics Reliability</i> , 1998 , 38, 1009-1013	1.2	1
24	Study of Cu diffusion in an Al ₁ wt.%Si _{0.5} wt.%Cu bond pad with an Al ₁ wt.%Si bond wire attached using scanning electron microscopy. <i>Microelectronics Reliability</i> , 1998 , 38, 309-315	1.2	4
23	The influence of addition elements on the early resistance changes observed during electromigration testing of Al metal lines. <i>Microelectronics Reliability</i> , 1998 , 38, 87-98	1.2	8
22	The dependence of stress induced voiding on line width studied by conventional and high resolution resistance measurements. <i>Microelectronics Reliability</i> , 1998 , 38, 1035-1040	1.2	
21	Comparison of the Electromigration Behavior of Al(MgCu) with Al(Cu) and Al(SiCu). <i>Materials Research Society Symposia Proceedings</i> , 1998 , 514, 133		1
20	Electromigration-Induced Drift in Damascene vs. Conventional Interconnects: An Intrinsic Difference. <i>Materials Research Society Symposia Proceedings</i> , 1998 , 516, 89		3
19	Stress relaxation in Al(Cu) thin films. <i>Microelectronic Engineering</i> , 1997 , 33, 137-147	2.5	7
18	The Effect of the Passivation Material on the Stress and Stress Relaxation Behavior of Narrow Al-Si-Cu Lines. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 428, 519		4
17	The isocurrent test: A promising tool for wafer-level evaluation of the interconnect reliability. <i>Microelectronics Reliability</i> , 1996 , 36, 1847-1850	1.2	5
16	Influence of the anti reflective coating on the electromigration resistance of 0.5 μ m technology metal-2 line structures. <i>Applied Surface Science</i> , 1995 , 91, 208-214	6.7	5
15	The Detrimental Effect of a Passivation on the Electromigration Lifetime of Narrow Al-Si-Cu Lines. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 391, 447		3
14	The viscosity of amorphous Pd-Si and Pd-Si/Pd-Si-Fe multilayers determined from stress relaxation in thin films on a substrate. <i>Journal of Applied Physics</i> , 1994 , 75, 1456-1462	2.5	3
13	Viscosity and elastic constants of amorphous Si and Ge. <i>Journal of Applied Physics</i> , 1993 , 74, 7154-7161	2.5	98

12	Determination of the plane stress elastic constants of thin films from substrate curvature measurements: Applications to amorphous metals. <i>Journal of Applied Physics</i> , 1993 , 73, 7344-7350	2.5	29
11	Bulk and interface stresses in silver-nickel multilayered thin films. <i>Journal of Applied Physics</i> , 1993 , 74, 2517-2523	2.5	132
10	Ti-W-N Deposition Stress as a Function of Microstructure. <i>Materials Research Society Symposia Proceedings</i> , 1993 , 308, 51		
9	Influence of temperature on the properties of sputtered AlSiCu films. <i>Applied Surface Science</i> , 1993 , 73, 295-304	6.7	1
8	Elastic Constants and Viscosity of Amorphous PdSi/PdSiFe Multilayers. <i>Materials Research Society Symposia Proceedings</i> , 1991 , 239, 121		5
7	The viscosity of amorphous metallic thin films. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 1991 , 134, 1274-1277	5.3	19
6	Determination Of Elastic Constants And Viscosity Of Amorphous Thin Films From Substrate Curvature. <i>Materials Research Society Symposia Proceedings</i> , 1990 , 188, 147		10
5	Viscosity, Structural Relaxation and Defect Annihilation Kinetics of Amorphous Si. <i>Materials Research Society Symposia Proceedings</i> , 1990 , 205, 21		9
4	Micromachining of pulsed laser annealed PECVD Si/sub x/Ge/sub 1-x/ deposited at temperatures /spl les/ 370/spl deg/C		2
3	Optimisation of PECVD poly-SiGe layers for MEMS post-processing on top of CMOS		4
2	Thin film encapsulation of acceleration sensors using polysilicon sacrificial layers		7
1	Self-aligned 0-level sealing of MEMS devices by a two layer thin film reflow process		2